

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	((("20030092233") or ("20030096501"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/24 11:02
S3	4	((("20030092233") or ("20030096501"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/24 11:03
S4	0	S3 and silicidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 11:03
S5	650	438/689,200,197,581,630,649, 651,655,682.ccls. and silicidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:47
S6	163	S5 and (reaction with silicon with metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:14
S7	14	S6 and (high adj dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:44
S11	90565	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:49
S13	1659525	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:50
S14	1659525	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:50

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S15	27538	S14 and MIS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 13:50
S16	27538	S14 and MIS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:09
S17	241	S16 and (silicidation salicidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:15
S18	234	S17 and (high (k dielectric constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:14
S19	39	S18 and pattern and etch\$4 and conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:11
S22	5085	S14 and (silicidation salicidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:14
S23	4823	S22 and (high (k dielectric constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:16
S24	693	S23 and pattern and etch\$4 and conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:16
S25	79	S24 and (reaction with silicon with metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:12
S26	654	S11 and (reaction with silicon with metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:12

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S27	235	S26 and (silicidation salicidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:14
S28	233	S27 and (high (k dielectric constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:14
S29	43	S28 and pattern and etch\$4 and conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 14:15
S30	654	S11 and (reaction with silicon with metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:14
S31	2113	S11 and ((reaction with silicon with metal) (silicidation salicidation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:15
S32	1694	S11 and (silicidation salicidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:15
S33	236	S32 and pattern and etch\$4 and conductor and (high (k dielectric constant)) and insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:31
S34	207	S32 and pattern and etch\$4 and conductor and (high (k dielectric constant)) and insulat\$4 and \$4mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/24 15:39
S35	58	S32 and pattern and etch\$4 and conductor and (high adj (k dielectric constant)) and insulat\$4 and \$4mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:26
S36	2180	"11" and (etch\$4 with substrate with insulating with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:32

## EAST Search History

S37	90634	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:31
S38	1695	S37 and (silicidation salicidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:31
S39	237	S38 and pattern and etch\$4 and conductor and (high (k dielectric constant)) and insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:31
S40	5	S39 and (etch\$4 with substrate with insulating with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:34
S41	14	S39 and ((etch\$4 near2 substrate) with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:45
S42	237	S39 and ((high dielectric constant insulating film) (high adj (k dielectric constant))on both ends of the conductor piece over the semiconductor "substrate.")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 14:47
S43	0	S39 and (((high dielectric constant insulating film) with (both end conductor piece))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/05/25 14:55
S44	0	S39 and (((high dielectric constant insulating film) or (high adj (k or dielectric or constant)))) with (both end conductor piece))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/05/25 14:56
S45	5	S39 and (((high dielectric constant insulating film) or (high adj (k or dielectric or constant)))) with etch\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/05/25 14:57
S46	6	((("20020047170") or ("20020052086") or ("20010028093")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/28 11:10